

<b>V<sub>DSS</sub> , 24V</b> <b>R<sub>DS(ON)</sub> , 7.7 mΩ (max.) @ V<sub>GS</sub>=4.5V</b> <b>R<sub>DS(ON)</sub> , 7.9 mΩ (max.) @ V<sub>GS</sub>=4.0V</b> <b>R<sub>DS(ON)</sub> , 8.8 mΩ (max.) @ V<sub>GS</sub>=3.1V</b> <b>R<sub>DS(ON)</sub> , 9.8 mΩ (max.) @ V<sub>GS</sub>=2.5V</b> <b>I<sub>D</sub> , 13A</b>	<b>DFN 3x3-8L</b>	

Description	Features
The SG2402TD uses advanced trench technology to provide excellent R <sub>DS(ON)</sub> , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.	<ul style="list-style-type: none"> <li>• Low On-Resistance</li> <li>• ESD Protection</li> <li>• Pb-free lead plating; RoHS compliant</li> </ul>
	<b>Applications</b> <ul style="list-style-type: none"> <li>• Load Switch</li> <li>• Battery Powered Systems</li> </ul>

### Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG2402TD	Halogen-Free	DFN 3x3-8L	TD	Tape & Reel	3,000

### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DS</sub>	24	V	
Gate-Source Voltage	V <sub>GS</sub>	±12	V	
Drain Current-Continuous	I <sub>D</sub>	13	A	
Drain Current-Pulsed <sup>Note 1</sup>	I <sub>DM</sub>	54	A	
Maximum Power Dissipation	Mounted on ceramic substrate (900mm <sup>2</sup> x 0.8mm) 1 unit	P <sub>D</sub>	2.7	W
	Mounted on ceramic substrate (900mm <sup>2</sup> x 0.8mm)	P <sub>T</sub>	2.7	W
Operating Junction Temperature Range	T <sub>J</sub> T <sub>STG</sub>	-55 to +150	°C	

### Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>Note 1</sup>	R <sub>θJA</sub>	Steady State	-	-	59	°C/W
Maximum Junction-to-Case	R <sub>θJC</sub>	Steady State	-	-	1.4	°C/W

#### Notes:

1. Pulse Test: Pulse Width ≤ 10μs, Duty Cycle ≤ 1%.
2. Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

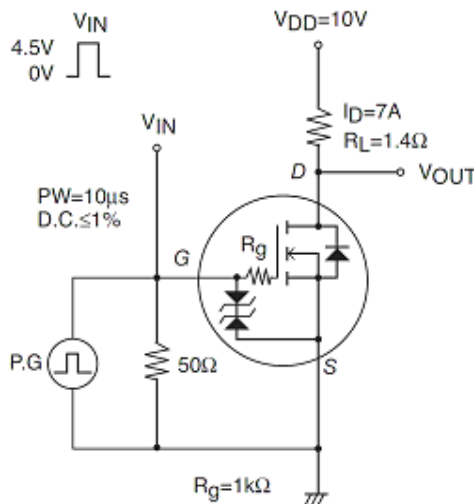
OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	24	27.5	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	-	-	±5	μA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA	0.45	0.6	1.3	V
Drain -Source On -State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =5.5A	-	6.7	7.7	mΩ
		V <sub>GS</sub> =4.0V, I <sub>DS</sub> =5.5A	-	6.9	7.9	
		V <sub>GS</sub> =3.1V, I <sub>DS</sub> =5.5A	-	7.5	8.8	
		V <sub>GS</sub> =2.5V, I <sub>DS</sub> =3.0A	-	8.2	9.8	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>DS</sub> =7A, V <sub>GS</sub> =4.5V, R <sub>g</sub> =1KΩ See Switching Time Test Circuit	-	0.56	-	μs
Rise Time	t <sub>r</sub>		-	0.54	-	
Turn-Off Delay Time	T <sub>d(off)</sub>		-	19	-	
Fall Time	t <sub>f</sub>		-	22	-	
Total Gate Charge at 4.5V	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>DS</sub> =13A, V <sub>GS</sub> =4.5V	-	13.2	-	nC
Gate to Source Gate Charge	Q <sub>GS</sub>		-	3.1	-	
Gate to Drain "Miller" Charge	Q <sub>GD</sub>		-	2.4	-	

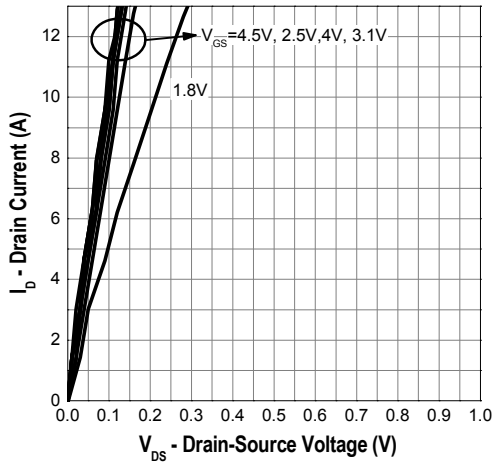
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =13A	-	0.7	1.2	V

**Switching Time Test Circuit**

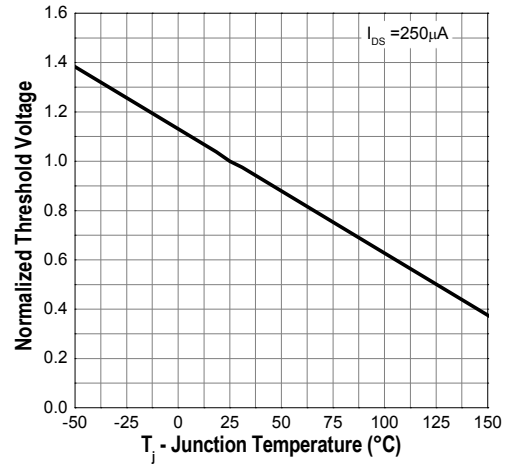


## Typical Operating Characteristics

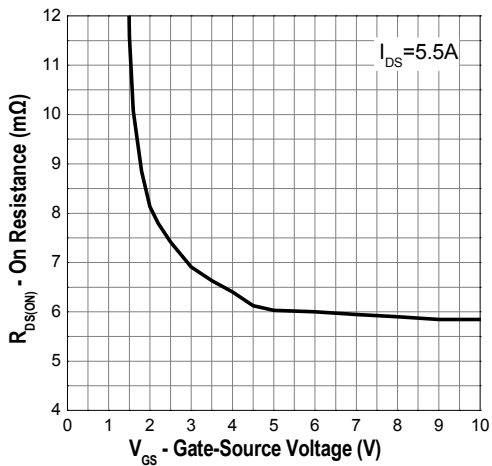
Output Characteristics



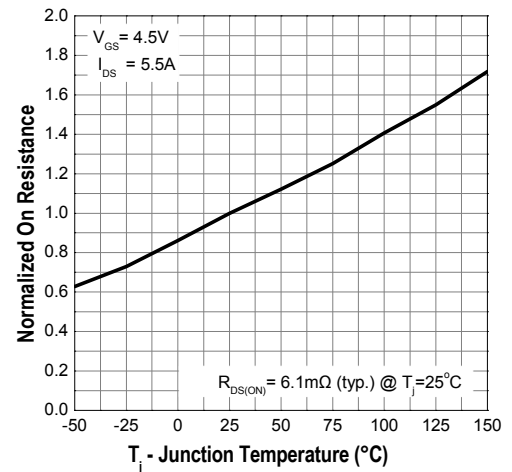
Gate Threshold Voltage



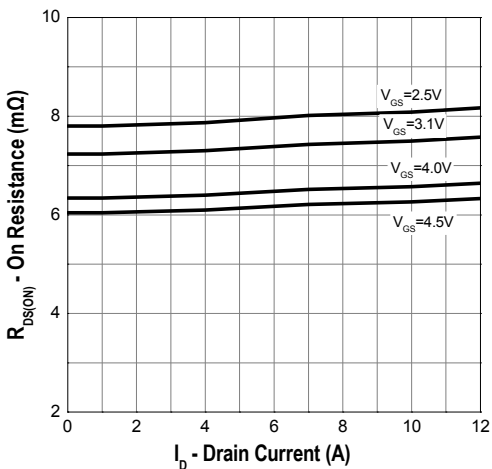
Gate-Source On Resistance



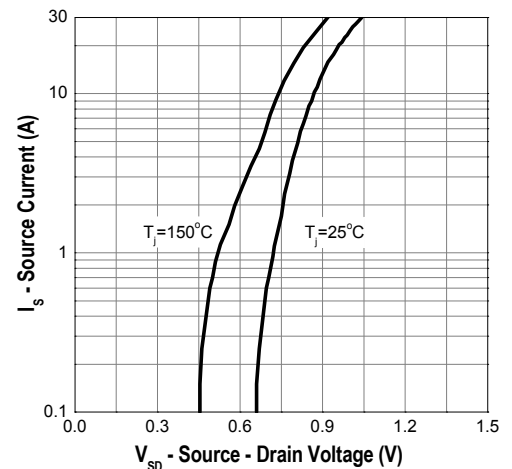
Drain-Source On Resistance



Drain-Source On Resistance

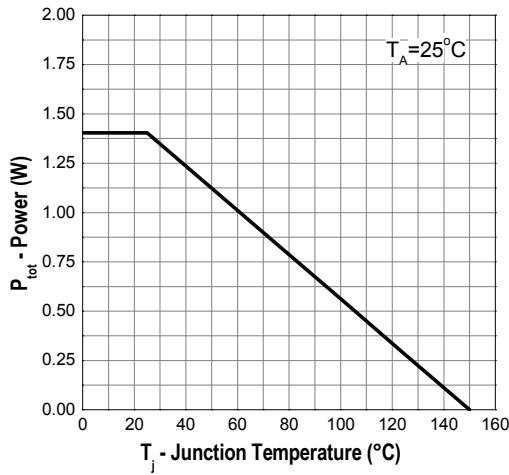


Source-Drain Diode Forward

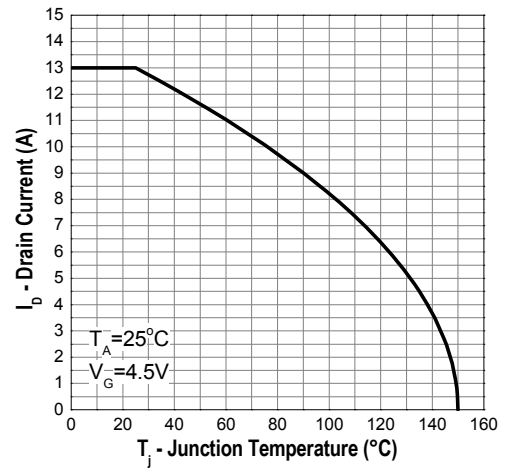


Typical Operating Characteristics (Cont.)

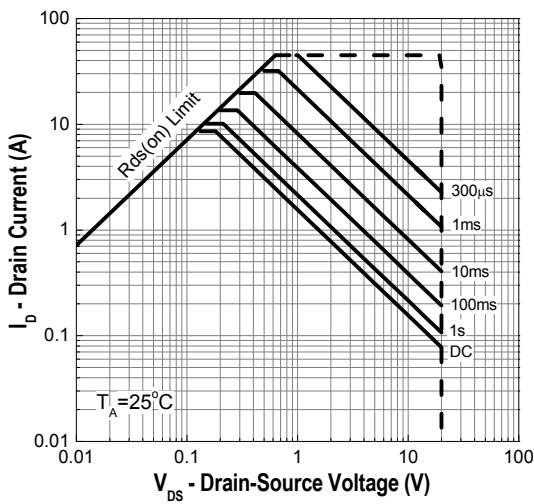
Power Dissipation



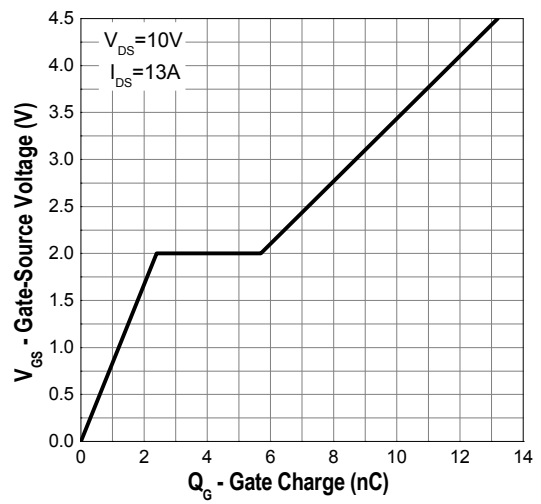
Drain Current




Safe Operation Area



Gate Charge

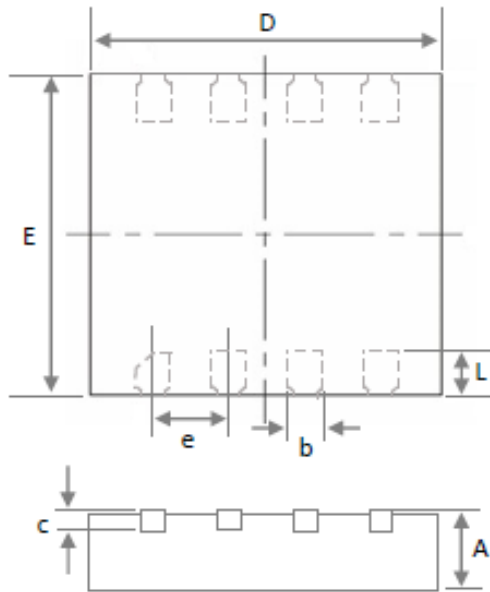


## Marking Information

DFN 3x3-8L (TD)	Marking Rule
<p data-bbox="89 353 256 387">Laser Marking</p> <div data-bbox="309 412 568 665" style="border: 1px solid black; padding: 10px; text-align: center;"> <p data-bbox="389 495 491 521"><b>2402TD</b></p> <p data-bbox="379 542 501 568"><b>YMMXXX</b></p>  </div> <p data-bbox="389 689 491 723">Diagram</p>	<p data-bbox="815 353 1066 387"><u>Line 1</u> : Device Name</p> <p data-bbox="815 407 906 441">2402TD</p> <p data-bbox="815 461 1043 495"><u>Line 2</u> : Date Code</p> <p data-bbox="815 515 932 548">YMMXXX</p> <p data-bbox="815 618 991 651">Y : Year Code</p> <p data-bbox="815 672 1034 705">MM : Month Code</p> <p data-bbox="815 725 1066 759">XXX : Serial Number</p>

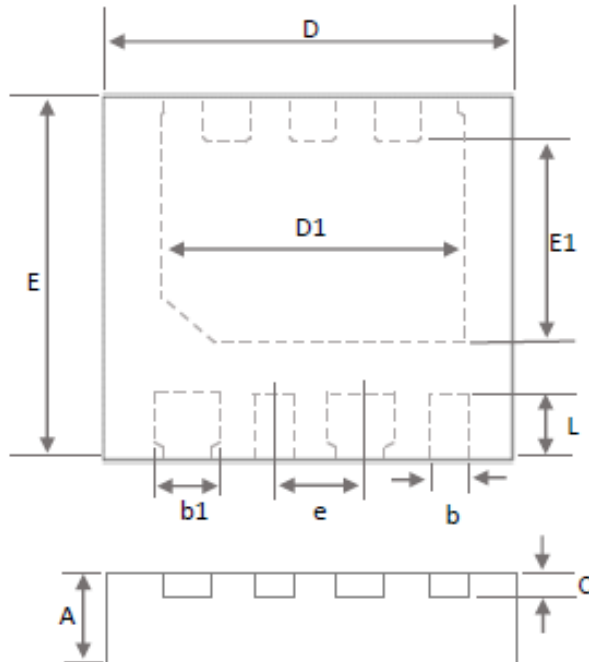
**Package Dimensions**

**T-TYPE**



Symbol	Min	Nor	Max
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.15	0.20	0.25
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
L	0.37	0.51	0.65
b1	0.45	0.50	0.55
E1	1.625	1.725	1.825
D1	2.20	2.30	2.40
e1	0.425	0.525	0.625

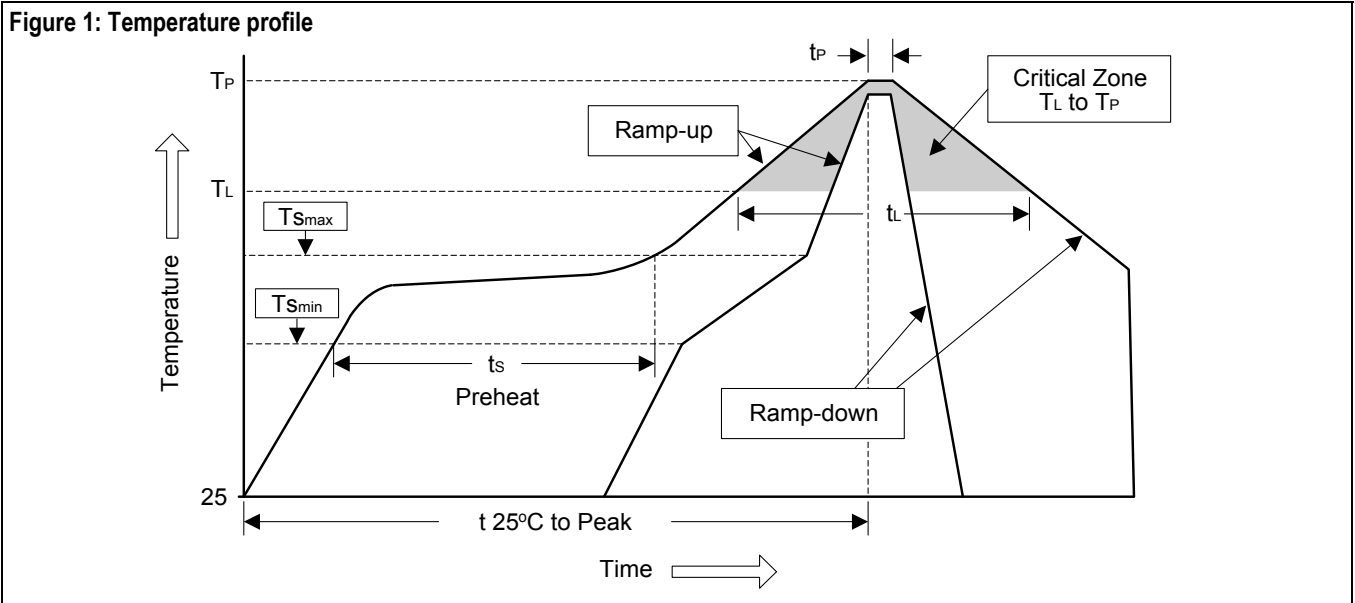
**S-TYPE**



1. All dimension are in millimeters.
2. Dimension dose not include burrs and mold flash/protrusions.

## Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min ( $T_{Smin}$ )	100°C	150°C
- Temperature Max ( $T_{Smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60 to 120 sec	60 to 180 sec
$T_{Smax}$ to $T_L$		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60 to 150 sec	60 to 150 sec
Peak Temperature ( $T_P$ )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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